DATA SHEET

BYD17 series
General purpose controlled avalanche rectifiers

Product specification
Supersedes data of 1999 Nov 11

2001 Oct 26

Philips Semiconductors

PHILIPS

General purpose controlled avalanche rectifiers

BYD17 series

FEATURES

- Glass passivated
- High maximum operating temperature
- Low leakage current
- Excellent stability
- Guaranteed avalanche energy absorption capability
- Shipped in 8 mm embossed tape
- Smallest surface mount rectifier outline.

DESCRIPTION

Cavity free cylindrical glass package through Implotec™(1) technology.

This package is hermetically sealed and fatigue free as coefficients of expansion of all used parts are matched.

(1) Implotec is a trademark of Philips.

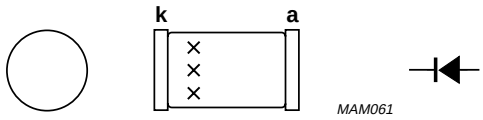


Fig.1 Simplified outline (SOD87) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	repetitive peak reverse voltage				
	BYD17D		–	200	V
	BYD17G		–	400	V
	BYD17J		–	600	V
	BYD17K		–	800	V
	BYD17M		–	1000	V
V_{RWM}	crest working reverse voltage				
	BYD17D		–	200	V
	BYD17G		–	400	V
	BYD17J		–	600	V
	BYD17K		–	800	V
	BYD17M		–	1000	V
V_R	continuous reverse voltage				
	BYD17D		–	200	V
	BYD17G		–	400	V
	BYD17J		–	600	V
	BYD17K		–	800	V
	BYD17M		–	1000	V

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$I_{F(AV)}$	average forward current	T_{tp} = 105 °C; averaged over any 20 ms period; see Figs 2 and 4	–	1.5	A
		T_{amb} = 65 °C; PCB mounting (see Fig.9); averaged over any 20 ms period; see Figs 3 and 4	–	0.6	A
I_{FSM}	non-repetitive peak forward current	t = 10 ms half sinewave; $T_j = T_{j\,max}$ prior to surge; $V_R = V_{RRMmax}$	–	20	A
E_{RSM}	non-repetitive peak reverse avalanche energy	L = 120 mH; $T_j = T_{j\,max}$ prior to surge; inductive load switched off	–	7	mJ
T_{stg}	storage temperature		–65	+175	°C
T_j	junction temperature	see Fig.5	–65	+175	°C

ELECTRICAL CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_F	forward voltage	I_F = 1 A; $T_j = T_{j\,max;}$ see Fig.6	–	–	0.93	V
		I_F = 1 A; see Fig.6	–	–	1.05	V
$V_{(BR)R}$	reverse avalanche breakdown voltage	I_R = 0.1 mA				
	BYD17D		225	–	–	V
	BYD17G		450	–	–	V
	BYD17J		650	–	–	V
	BYD17K		900	–	–	V
	BYD17M		1100	–	–	V
I_R	reverse current	$V_R = V_{RRMmax}$; see Fig.7	–	–	1	µA
		$V_R = V_{RRMmax}$; T_j = 165 °C; see Fig.7	–	–	100	µA
t_{rr}	reverse recovery time	when switched from I_F = 0.5 A to I_R = 1 A; measured at I_R = 0.25 A; see Fig.10	–	3	–	µs
C_d	diode capacitance	V_R = 0 V; f = 1 MHz; see Fig.8	–	21	–	pF

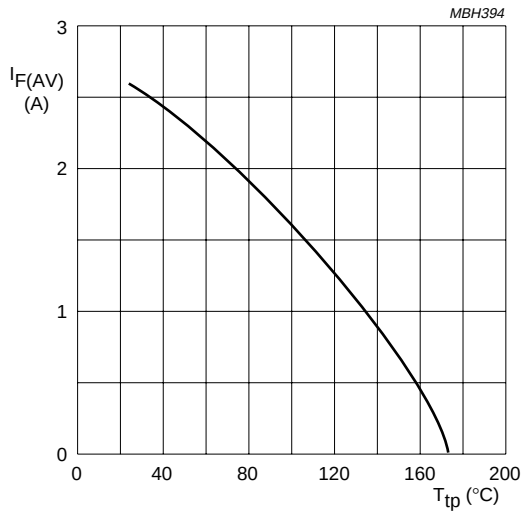
THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\,j\text{-}tp}$	thermal resistance from junction to tie-point		30	K/W
$R_{th\,j\text{-}a}$	thermal resistance from junction to ambient	note 1	150	K/W

Note

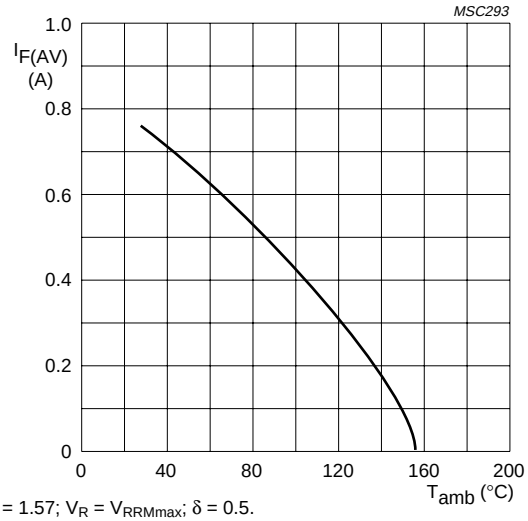
1. Device mounted on epoxy-glass printed-circuit board, 1.5 mm thick; thickness of copper ≥40 µm, see Fig.9. For more information please refer to the *"General Part of associated Handbook"*.

GRAPHICAL DATA



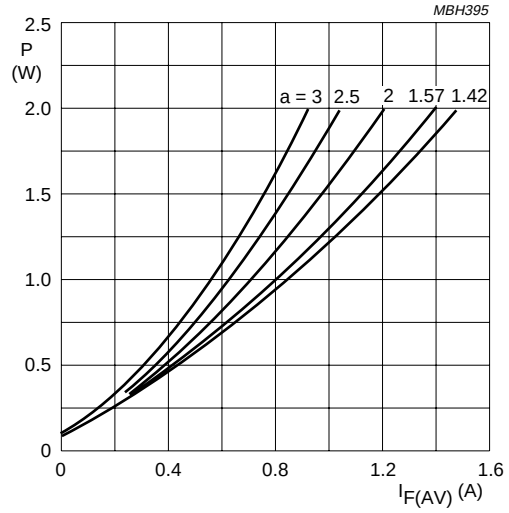
a = 1.57; $V_R = V_{RRMmax}$; δ = 0.5.

Fig.2 Maximum permissible average forward current as a function of tie-point temperature (including losses due to reverse leakage).



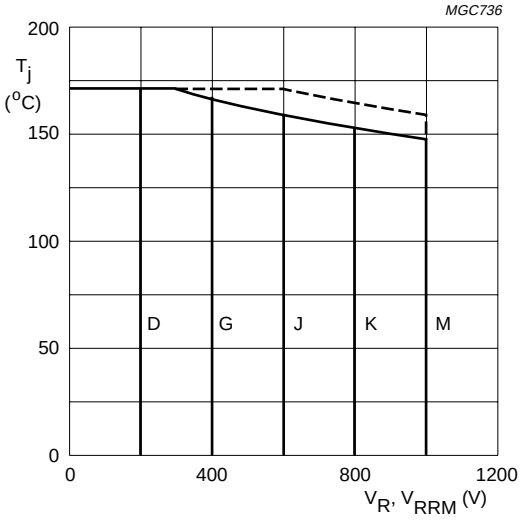
a = 1.57; $V_R = V_{RRMmax}$; δ = 0.5.
Device mounted as shown in Fig.9.

Fig.3 Maximum permissible average forward current as a function of ambient temperature (including losses due to reverse leakage).



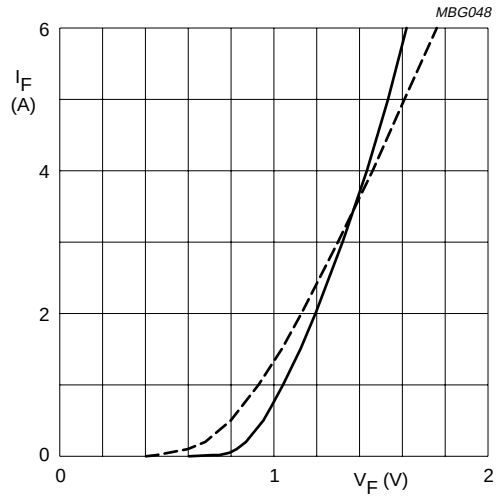
a = $I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RRMmax}$; δ = 0.5.

Fig.4 Maximum steady state power dissipation (forward plus leakage current losses, excluding switching losses) as a function of average forward current.



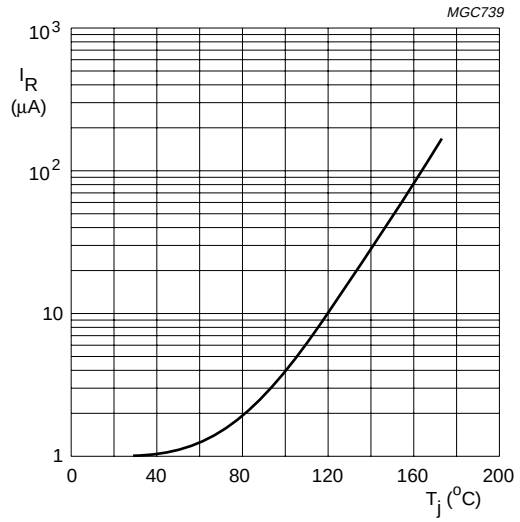
Solid line = V_R.
Dotted line = V_{RRM}; δ = 0.5.

Fig.5 Maximum permissible junction temperature as a function of reverse voltage.



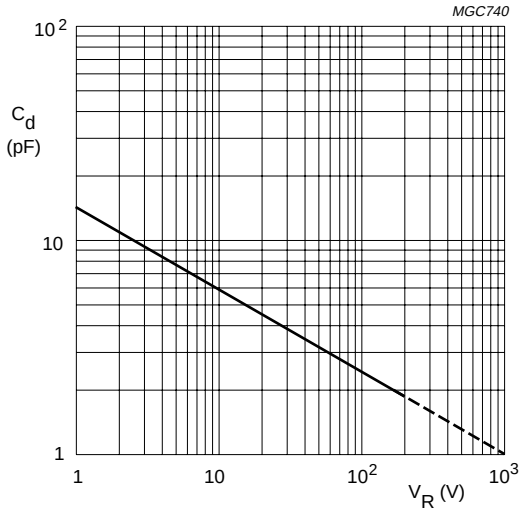
Solid line: T_j = 25 °C.
Dotted line: T_j = 175 °C.

Fig.6 Forward current as a function of forward voltage; maximum values.



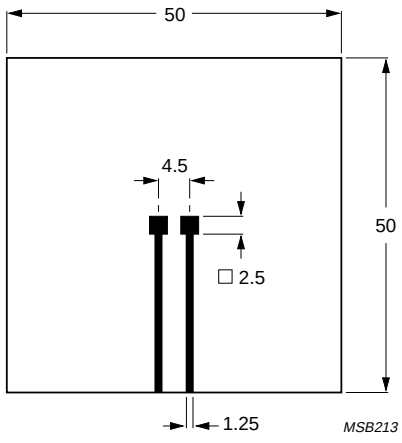
$V_R = V_{RRMmax.}$

Fig.7 Reverse current as a function of junction temperature; maximum values.



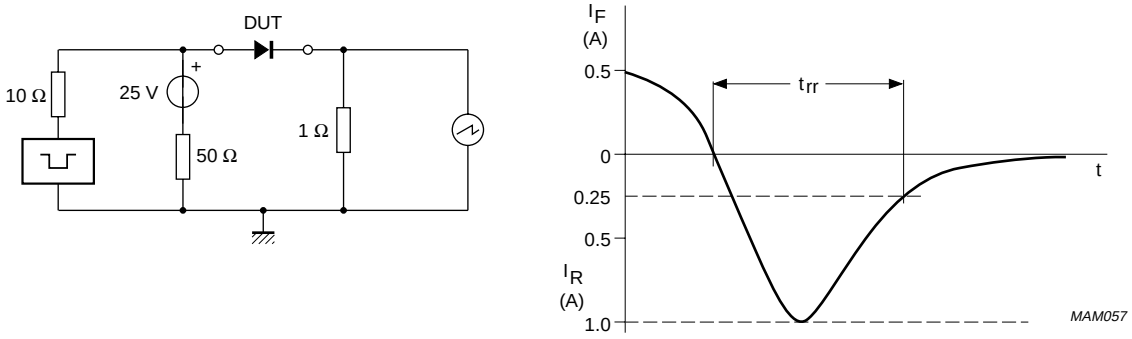
f = 1 MHz; T_j = 25 °C.

Fig.8 Diode capacitance as a function of reverse voltage; typical values.



Dimensions in mm.

Fig.9 Printed-circuit board for surface mounting.

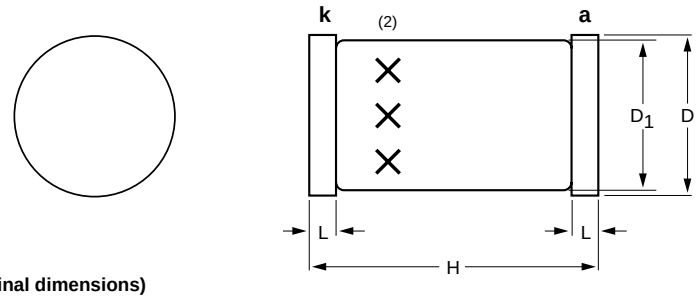


Input impedance oscilloscope: 1 MΩ, 22 pF; $t_r \leq 7$ ns.
Source impedance: 50 Ω; $t_r \leq 15$ ns.

Fig.10 Test circuit and reverse recovery time waveform and definition.

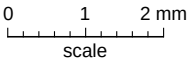
PACKAGE OUTLINE

Hermetically sealed glass surface mounted package;
Implotec™(1) technology; 2 connectors **SOD87**



DIMENSIONS (mm are the original dimensions)

UNIT	D	D1	H	L
mm	2.1 2.0	2.0 1.8	3.7 3.3	0.3



Notes

1. Implotec is a trademark of Philips.
2. The marking indicates the cathode.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOD87	100H03					~~99-03-31~~ 99-06-04

DATA SHEET STATUS

DATA SHEET STATUS[1]	PRODUCT STATUS[2]	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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